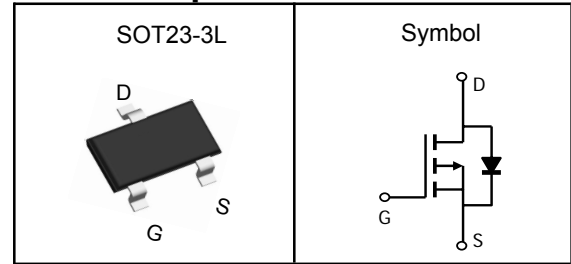


## P-Channel Enhancement Mode MOSFET

### Features

- Low Rdson for low conduction loss
- Reliable and Rugged
- ROHS Compliant & Halogen-Free

### Pin Description



### Applications

- Power Management in Desktop Computer
- DC/DC Converters

V <sub>bss</sub>	-20	V
R <sub>DS(ON)-Typ</sub>	25	mΩ
I <sub>D</sub>	-6	A

### Absolute Maximum Ratings (T<sub>J</sub>=25°C, Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
V <sub>bss</sub>	Drain-Source Voltage	-20	V
V <sub>GSS</sub>	Gate-Source Voltage	±12	V
T <sub>J</sub>	Maximum Junction Temperature	-55 to 150	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
I <sub>DM</sub> <sup>①</sup>	Pulse Drain Current Tested	T <sub>c</sub> =25°C -24	A
I <sub>D</sub>	Continuous Drain Current	T <sub>c</sub> =25°C -6	A
P <sub>D</sub>	Maximum Power Dissipation	T <sub>c</sub> =25°C 1.2	W

### Thermal Characteristics

Symbol	Parameter	Rating	Unit
R <sub>θJA</sub> <sup>③</sup>	Thermal Resistance-Junction to Ambient	100	°C/W

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C.

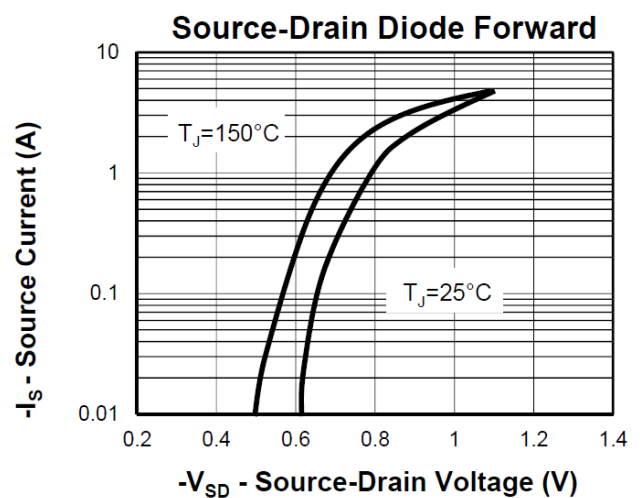
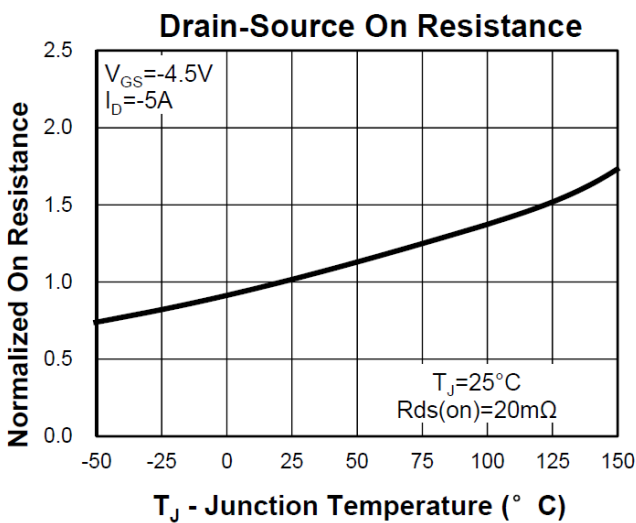
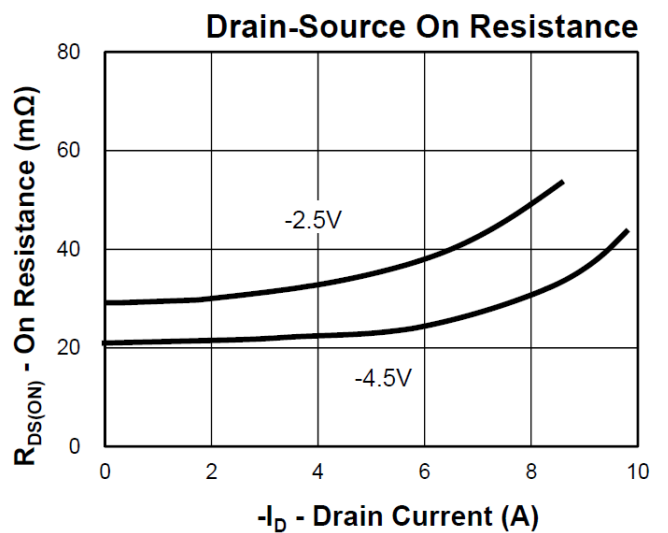
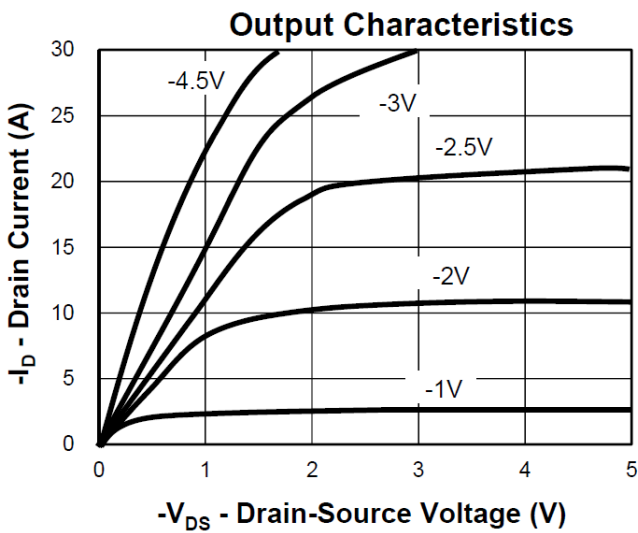
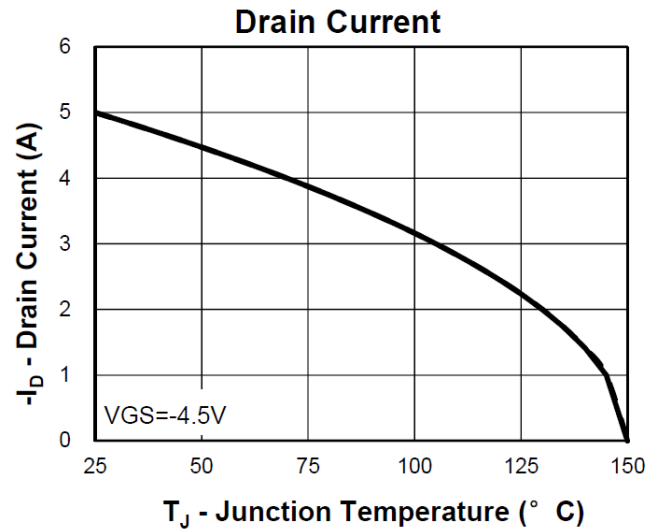
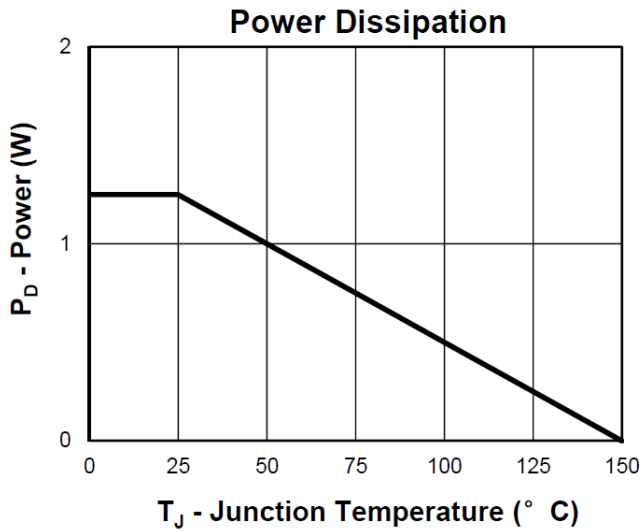
Note ③ : Surface Mounted on 1in<sup>2</sup> FR-4 board with 1oz.

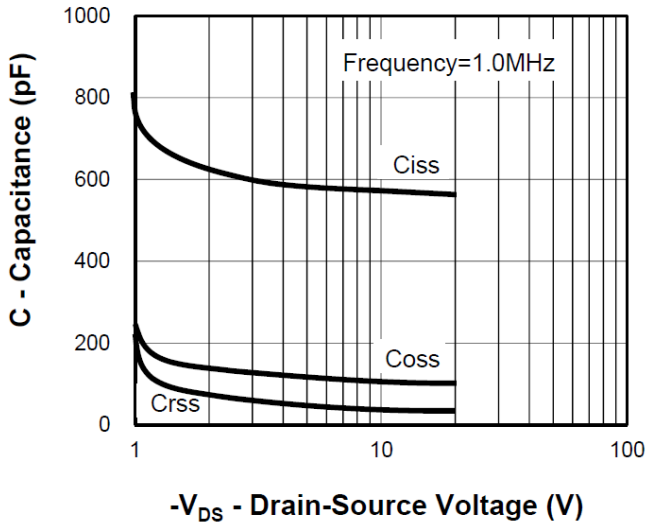
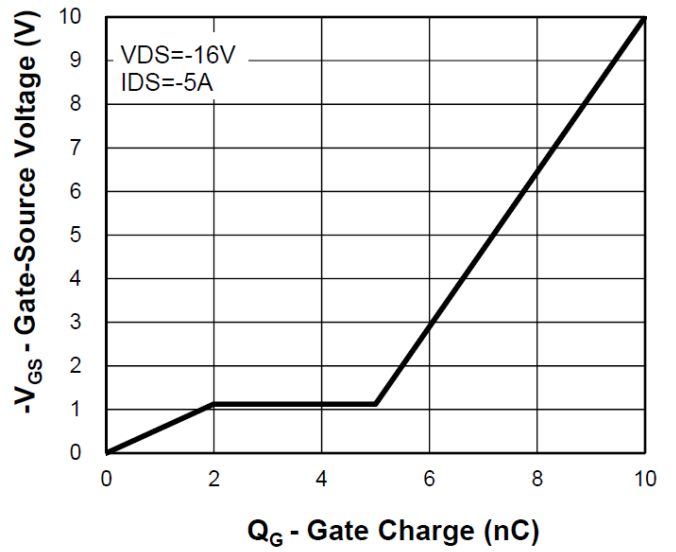
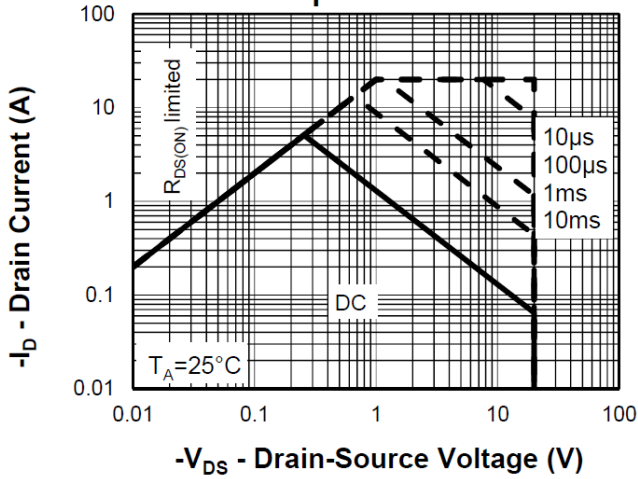
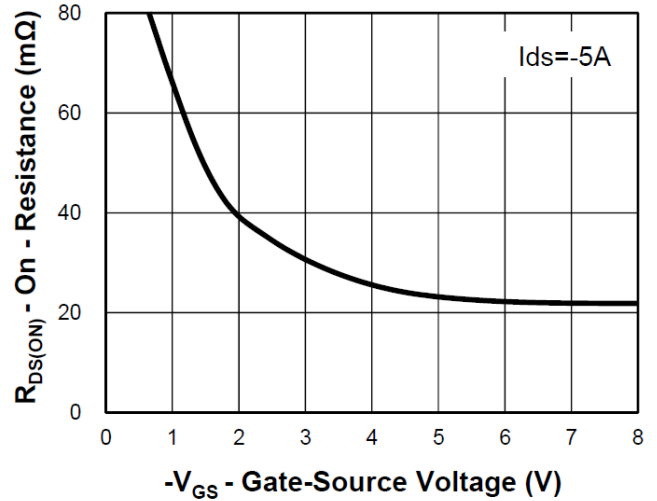
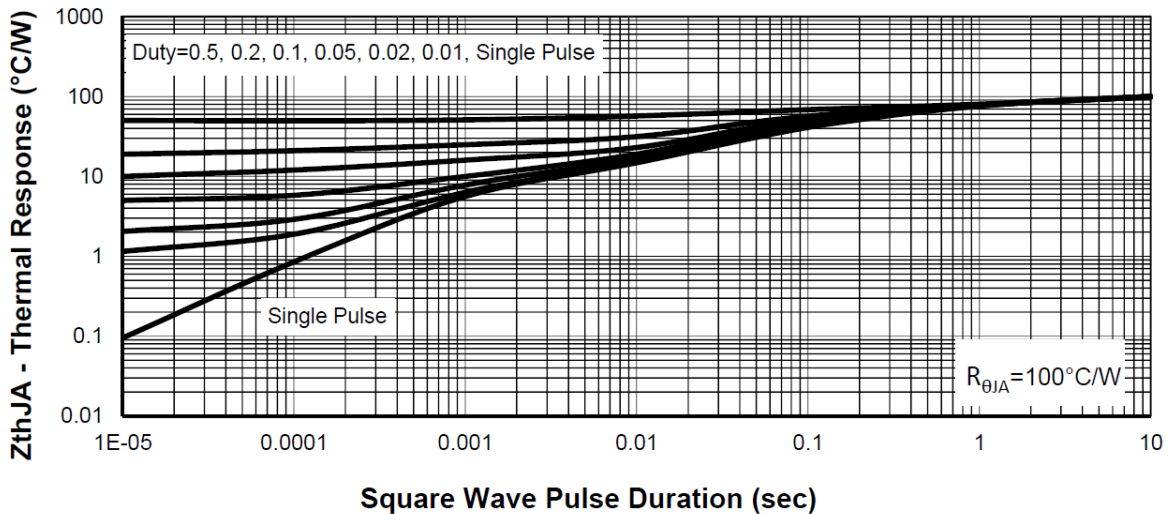
**P-Channel Enhancement Mode MOSFET****Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$ , Unless Otherwise Noted)

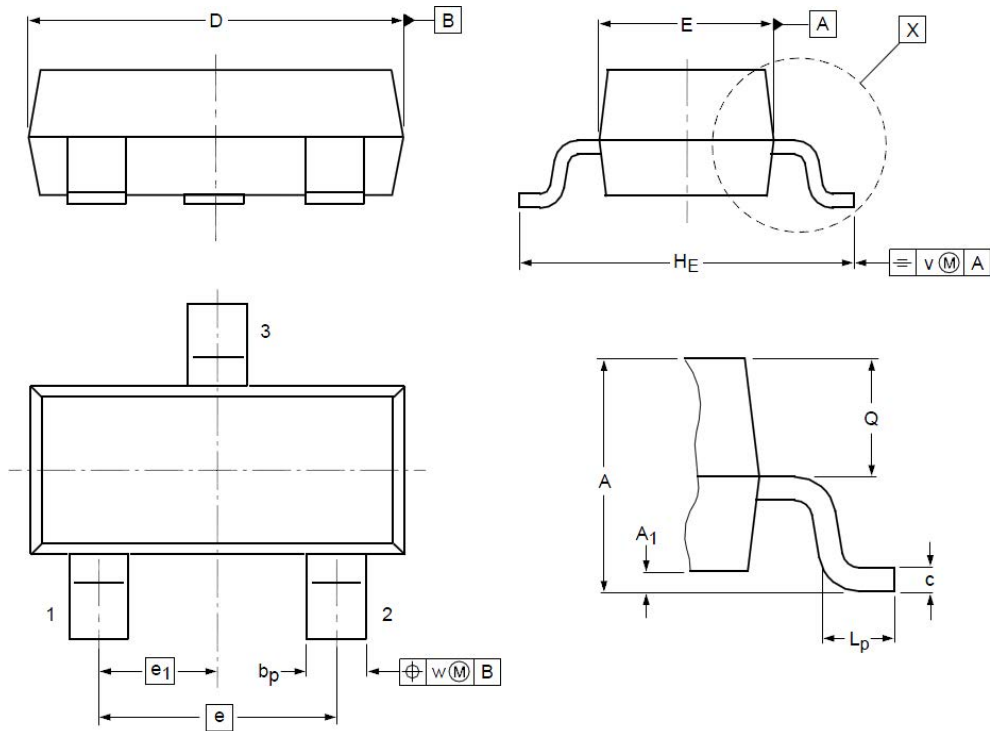
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Static Electrical Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	---	---	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-20V, V_{GS}=0V$	---	---	-1	$\mu A$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5	---	-1.0	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	---	---	$\pm 100$	nA
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS}=-4.5V, I_D=-5A$	---	17	20	m $\Omega$
		$V_{GS}=-2.5V, I_D=-3A$	---	20	25	
gfs	Forward Transconductance	$V_{DS}=-5V, I_D=-6A$	---	5	---	S
<b>Dynamic Characteristics</b> <sup>⑤</sup>						
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=-10V,$ Freq.=1MHz	---	2100	---	pF
$C_{oss}$	Output Capacitance		---	498	---	
$C_{rss}$	Reverse Transfer Capacitance		---	300	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=-10V, I_D=-2.8A,$ $V_{GS}=-4.5V, R_G=6\Omega,$ $R_L=10\Omega$	---	25	---	nS
$T_r$	Turn-on Rise Time		---	30	---	
$T_{d(off)}$	Turn-off Delay Time		---	70	---	
$T_f$	Turn-off Fall Time		---	50	---	
$Q_g$	Total Gate Charge	$V_{GS}=-10V, V_{DS}=-4.5V,$ $I_D=-6A$	---	17	---	nC
$Q_{gs}$	Gate-Source Charge		---	4.1	---	
$Q_{gd}$	Gate-Drain Charge		---	4.3	---	
<b>Source-Drain Characteristics</b>						
$V_{SD}$ <sup>④</sup>	Diode Forward Voltage	$I_S=-1.25A, V_{GS}=0V$	---	-0.81	-1.2	V

Note ④: Pulse test (pulse width 300us, duty cycle 2%).

Note ⑤: Guaranteed by design, not subject to production testing.

**P-Channel Enhancement Mode MOSFET**
**Typical Characteristics**


**P-Channel Enhancement Mode MOSFET**
**Capacitance**

**Gate Charge**

**Safe Operation Area**

**Drain Current**

**Thermal Transient Impedance**


**P-Channel Enhancement Mode MOSFET**
**SOT23-3L Package Outline Dimensions**


Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
<b>A</b>	0.90	1.07	1.25	<b>e<sub>1</sub></b>	--	0.95	--
<b>A<sub>1</sub></b>	0.01	0.05	0.10	<b>H<sub>E</sub></b>	2.50	2.80	3.00
<b>b<sub>p</sub></b>	0.30	0.40	0.50	<b>L<sub>p</sub></b>	0.30	0.45	0.60
<b>c</b>	0.10	0.15	0.20	<b>Q</b>	0.23	0.28	0.33
<b>D</b>	2.70	2.90	3.10	<b>V</b>	--	0.20	--
<b>E</b>	1.40	1.55	1.75	<b>W</b>	--	0.20	--
<b>e</b>	--	1.90	--				